

[TuA2] Low-Dimensional Materials

Session Date	July 14 (Tue.), 2026
Session Time	10:35–12:20
Session Room	Room A (Baekrok Hall A, 1F)
Session Chairs	Prof. Zaichun Sun (Wuhan University of Technology, China), Prof. Lars Samuelson (Southern University of Science and Technology, China)

[TuA2–1] [Invited]

10:35–11:05

Telecom C-Band InAs Quantum Dots on GaAs for Quantum Technological Application

Michael Jetter, Ponraj Vijayan, Stephanie Bauer, Robert Sittig, Raphael Joos, Nam Tran, Cornelius Nawrath, Sascha Kolatschek, Simone Luca Portalupi, and Peter Michler, University of Stuttgart, Germany

[TuA2–2]

11:05–11:20

Interlayer-Free Self-Assembled Growth of GaN Nanorods on Si Substrate for White Light-Emitting Diode

Ameer Abdullah¹, Jeong Ho¹, Sang-Wan Ryu², and Yong Hoon Cho¹, ¹Korea Advanced Institute of Science and Technology, Korea, ²Chonnam National University, Korea

[TuA2–3]

11:20–11:35

Exploring the MOVPE Growth of Droplet Epitaxy InAs/InP Quantum Dots for Quantum Photonic Applications

Elisa M. Sala¹, Young In Na¹, Raja S.R. Gajjala², Edoardo G. Banfi², Guoliang Zhou¹, Paul M. Koenraad², and Jon Heffernan¹, ¹The University of Sheffield, United Kingdom, ²Eindhoven University of Technology, Netherlands

[TuA2–4]

11:35–11:50

Growth of InGaAs Quantum Dots on GaAs with Emission at C-Band Wavelengths

Juwana Jose, David Nguyen, Christoph Berger, Jürgen Bläsing, Armin Dadgar, and André Strittmatter, Otto von Guericke University, Germany

[TuA2-5]

11:50-12:05

Robust GaAs/SiO₂/Si Wafer-Bonded Templates for Monolithic Telecom C-Band InAs Quantum Dot Single-Photon Sources on Silicon

P. Vijayan, M. Seidel, M. Jetter, and P. Michler, Universität Stuttgart, Germany

[TuA2-6]

12:05-12:20

MOVPE of Ga(Sb,Bi)/GaSb Heterostructures on GaSb Nano-Ridges

Marcel Kröner¹, Michiel de Maeyer^{2,3}, Johannes Haust¹, Andreas Beyer¹, Bernardette Kunert², and Kerstin Volz¹, ¹Philipps-Universität Marburg, Germany, ²imec, Belgium, ³Ghent University, Belgium